DESCRIPTION

~~EVALUATION METHOD AND PRODUCTION METHOD FOR SEMICONDUCTOR WAFERS~~

TECHNICAL FIELD

[0001]

The present invention relates to a semiconductor-wafer evaluation method and a manufacturing method by using the same.

BACKGROUND ART

[0002]

A manufacturing method of a semiconductor wafer, such as a silicon single crystal wafer, generally includes a slicing step of slicing a single crystal ingot obtained by the Czochralski method (CZ method) into a thin disk wafers; a chamfering step of chamfering an outer circumferential portion to prevent breakage and chips of the wafer; a lapping step of flattening the wafer; an etching step of removing process strain residing in a surface layer of the wafer due to these steps; a mirror-polishing step of polishing a wafer surface into a mirror surface; and a cleaning step of removing contaminants such as a polishing agent and extraneous substances attached in the polishing step. A heat treatment or a grinding step other than the above steps may be added, the order of the steps may be changed, or the same step may be performed multiple times, as needed.

[0003]

In recent years, a sallow trench isolation (STI) process or the other process is used as a minute device

DESCRIPTION

SEMICONDUCTOR WAFER EVALUATION METHOD AND SEMICONDUCTOR WAFER MANUFACTURING METHOD

TECHNICAL FIELD

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